汕头华汕电子器件有限公司

N-Channel Enhancement Mode Field Effect Transistor

HFF8N60

对应国外型号
FQPF8N60C

■ 主要用途

高速开关应用。

■ 极限值（T_a=25℃）

T_{stg}——贮存温度…… -55~150℃

T_j——结温…… 150℃

V_{DSS}——漏极—源极电压……600V

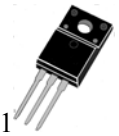
V_{GS}——栅极—源极电压…… ±30V

I_D——漏极电流（T_c=25℃）……7.5A

P_D——耗散功率（T_c=25℃）……48W

■ 外形图及引脚排列

TO-220F



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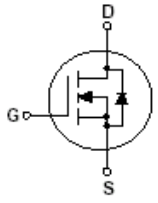
1—栅 极 G
2—漏 极 D
3—源 极 S



■ 电参数（T_a=25℃）

参数符号	符 号 说 明	最小值	典型值	最大值	单 位	测 试 条 件
BV_{DSS}	漏—源极击穿电压	600			V	I_D=250μA ,V_{GS}=0V
I_{DSS}	零栅压漏极电流			1	μA	V_{DS} =600V， V_{GS}=0
I_{GSS}	栅极泄漏电流			±100	nA	V_{GS}=±30V , V_{DS} =0V
$V_{GS(th)}$	栅—源极开启电压	2.0		4.0	V	V_{DS} = V_{GS} , I_D =250μA
$R_{DS(on)}$	漏—源极导通电阻		1.0	1.2	Ω	V_{GS}=10V, I_D =3.75A
gfs	正向跨导		8.7		S	V_{DS} = 40V , I_D=3.75A *
Ciss	输入电容		965	1255	pF	
Coss	输出电容		105	135	pF	V_{DS} =25V, V_{GS}=0,f=1MHz
Crss	反向传输电容		12	16	pF	
$t_{d(on)}$	导通延迟时间		16.5	45	nS	
tr	上升时间		60.5	130	nS	V_{DD} =300V,
$t_{d(off)}$	断开延迟时间		81	170	nS	I_D =7.5A (峰值)
t_f	下降时间		64.5	140	nS	R_G= 25 Ω *
Qg	栅极总电荷		28	36	nC	V_{DS} =480V
Qgs	栅极—源极电荷		4.5		nC	V_{GS}=10V
Qgd	栅极—漏极电荷		12		nC	I_D=7.5A *
Is	源极—漏极二极管正向电流			7.5	A	
V_{SD}	源极—漏极二极管导通电压			1.4	V	I_S =7.5A , V_{GS}=0
Rth（j-c）	热阻			2.6	℃/W	结到外壳

*注：脉冲测试，宽度≤300μS, 占空比≤2%

■ 特性曲线

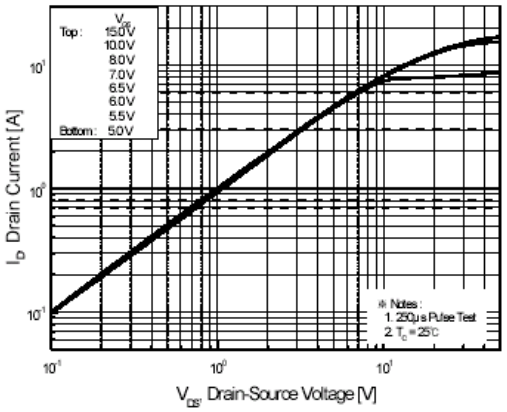


Figure 1. On-Region Characteristics

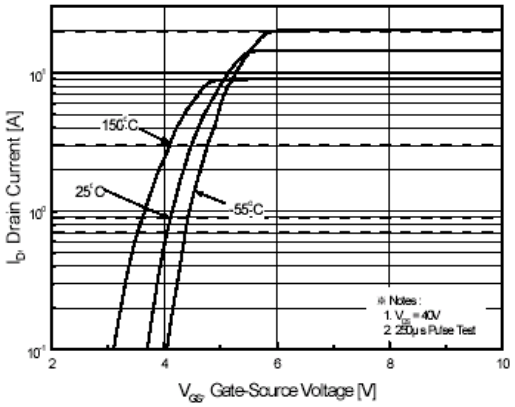


Figure 2. Transfer Characteristics

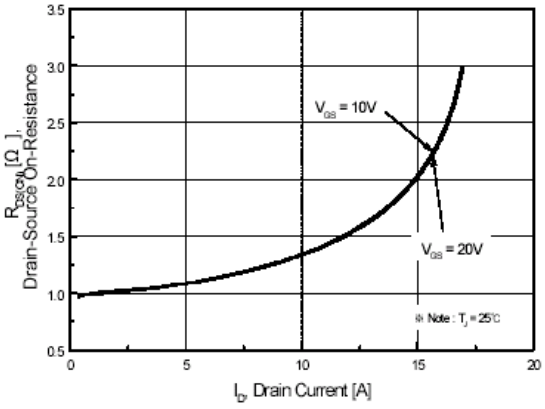


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

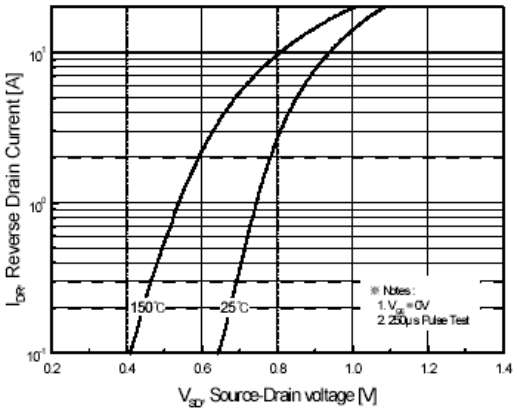


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

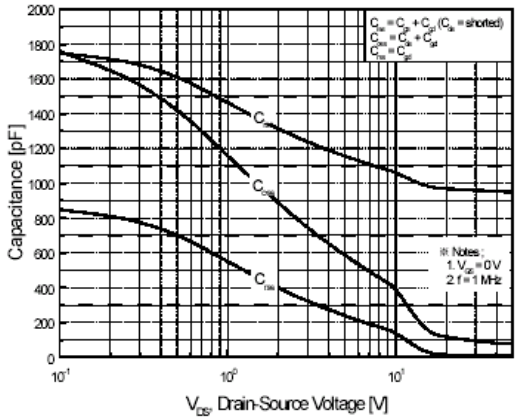


Figure 5. Capacitance Characteristics

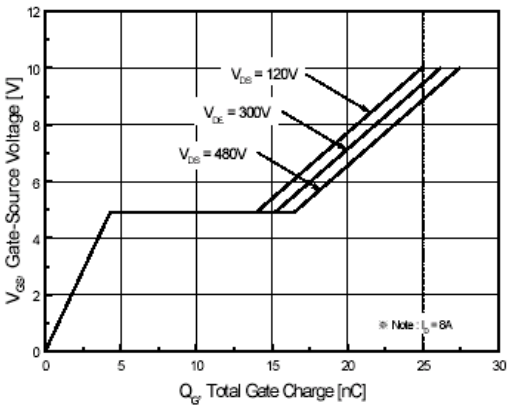


Figure 6. Gate Charge Characteristics

■ 特性曲线

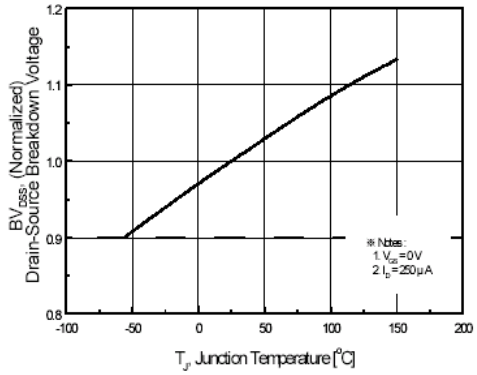


Figure 7. Breakdown Voltage Variation vs Temperature

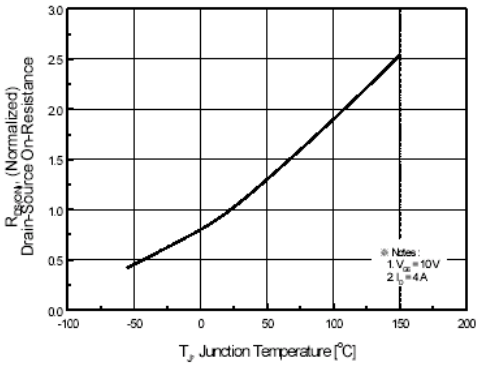


Figure 8. On-Resistance Variation vs Temperature

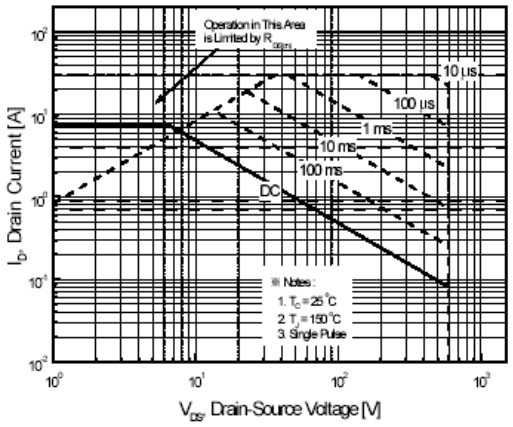


Figure 9 Maximum Safe Operating Area for HFF8N60

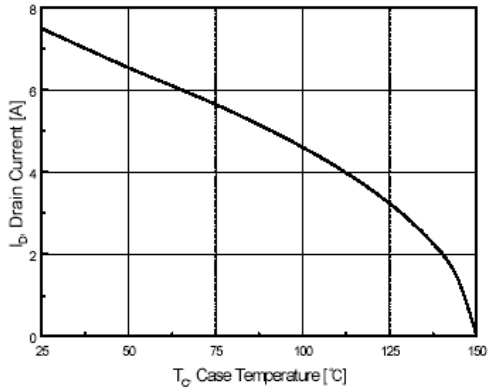


Figure 10. Maximum Drain Current vs Case Temperature

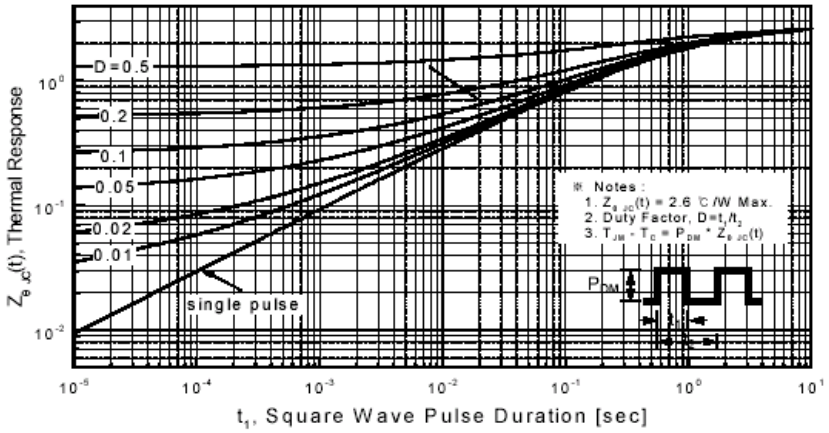
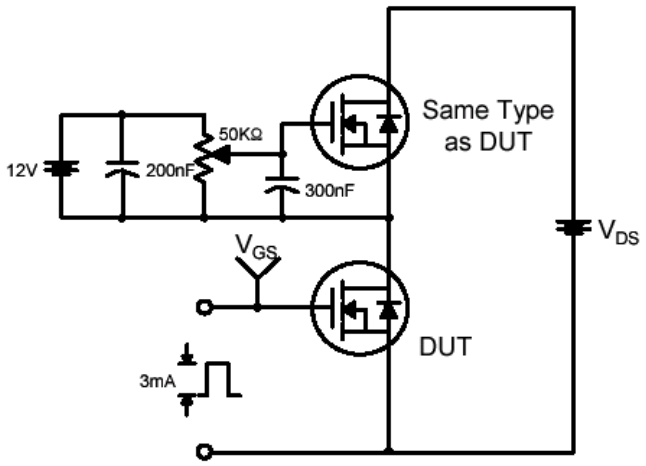
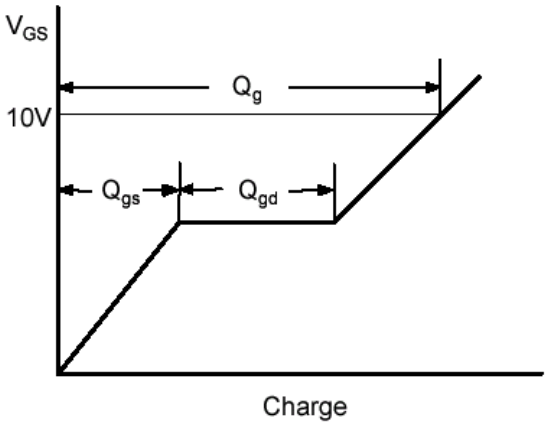


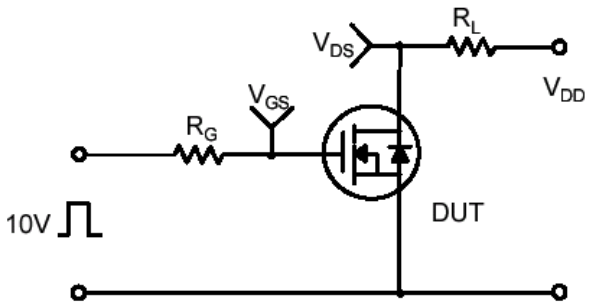
Figure 11-2. Transient Thermal Response Curve for HFF8N60

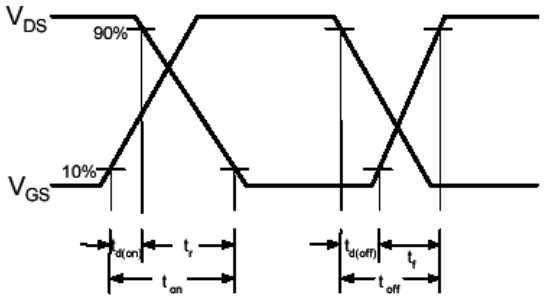
Gate Charge Test Circuit & Waveform



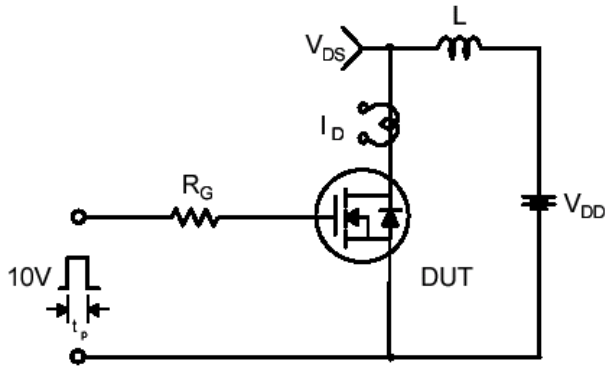


Resistive Switching Test Circuit & Waveforms

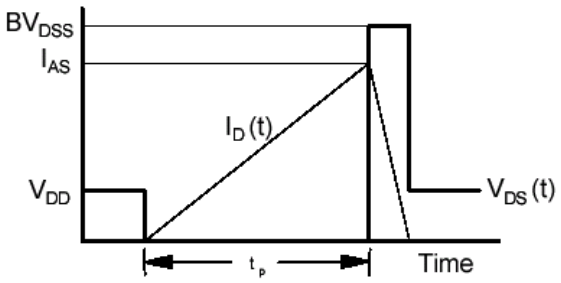




Unclamped Inductive Switching Test Circuit & Waveforms



$$E_{AS} = \frac{1}{2} L I_{AS}^2 \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$



Peak Diode Recovery dv/dt Test Circuit & Waveforms